Self-cooling cryogenic microcalorimeters made of STJ junctions

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Abstract

High quality low leakage STJ devices made of Al-AlMn-Al layers were fabricated for energy dispersive single photon detection. Information on different heat flow channels was extracted from the measured dynamics of detector signals due to X-ray events. At the optimum operation point, the extracted effective electron temperature decreased from 88 mK down to 43 mK due to self-cooling, roughly doubling the detector sensitivity.

Key words: Microcalorimeter, Cryogenic detector, Tunnel junction, Microfabrication, Self-cooling
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Energy resolving single photon detectors are of great interest for astrophysics, material science, medical applications or any other field, where high quantum efficiency paired with direct energy information are desirable. Cryogenic microcalorimeters based on normal metal–insulator–superconductor (NIS) junctions are very attractive and proven candidates for such high resolution detectors [1]. Essential requirements for NIS spectrometers are low barrier leakage currents and operation at low temperatures for a small heat capacity of the absorber. The latter can be met or improved by the Peltier-like effect of hot-electron tunneling [2,3,4]. The efficiency of power transfer out of the absorber is increased by coupling the normal metal symmetrically via two tunnel junctions in series [5] (STJ structure). Heat flow mechanisms upon energy deposition are reflected by detector signal dynamics.

We have fabricated high quality STJ junctions by standard optical lithography and metal evaporation deposition (see inset of Fig. 1 for schematic drawing). The superconducting electrodes were pure Aluminium (Al, 300 nm thick), whereas the normal absorber was Al doped with 0.3–0.6% of Manganese (Mn, 10–500 nm thick) in order to suppress Cooper pairing [6]. An additional Silver layer (0.1–8 μm) was eventually deposited on top of the AlMn absorber in order to increase absorption efficiency to X-rays. The native AlO_x forming the tunnel barrier yielded excellent and highly stable device characteristics with very low leakage currents. The product of (single) junction area A and normal resistance R_n was $_n = R_nA = 0.6$–40 k$\Omega\,\mu m^2$ for different oxide thicknesses. Figure 1 shows current-voltage characteristics of a high $_n$ device together with its differential resistance $R_d = @V=@I$. The measured gap corresponds to twice the Al gap ($_{Al} = 172$ eV). This fact and the perfect symmetry of the characteristics indicate no significant influence of the Mn doping

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on tunneling current. Low leakage is required for current biased detector operation. From extrapolation of the voltage dependent low current R_d to $V \to 0$ we extract a device base temperature of $T_b = 88$ mK, in spite of a cryostat temperature of about 50 mK. The elevated T_b is due to background blackbody radiation and the presence of a relatively powerful ^{55}Fe X-ray source. The ratio of leakage resistance to R_n was $5.6 \cdot 10^5$ for the device in Fig. 1 (representative for high $_n$ samples) and decreased moderately for increasing barrier transparency (lower $_n$).

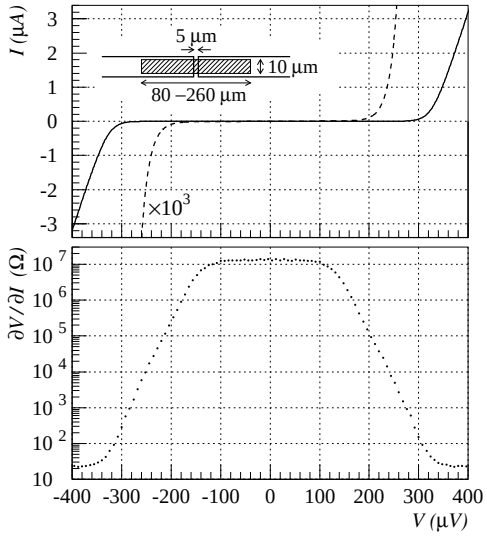

Fig. 1. Measured current-voltage characteristics (solid line top graph) and corresponding differential resistance (bottom) of a high $_n$ SINIS device, a schematic drawing of which is shown in the inset. The dashed line (top graph) represents the same data but with current scaled by 10^3.

Upon energy deposition in the absorber and (presumably quick) energy transfer to the electron system the heat flow is dominated by [7]:

- Electron-phonon coupling. The (hot) electrons relax to the (cold) phonon bath with a rate [8]

$$P_{e\ ph} = \quad (T_e^5 \quad T_b^5); \qquad (1)$$

  where $\quad 3$ nW K^{-5} m^{-3} is a material dependent coupling constant and $\quad$ is the absorber volume.
- Hot-electron tunneling. The excess quasiparticles excited above the gap are extracted yielding the desired current signal. Power is removed irrespective of electrical current flow direction (i.e. through both junctions) and is approximately given (per junction) by

$$P_{tun} \quad \frac{I}{e} \max(\quad eV; kT): \qquad (2)$$

- Backheating. Excitations which are not efficiently removed from the barrier region can leak back to the absorber volume [7].
- Power load from background radiation sources. Here we estimate $P_{bg} \quad 160$ pW.

The thermal conductances $G = dP/dT$ determine the time constants $= C(T)/G$ of the relaxation processes, where $C(T) = T$ is the electronic specific heat and the Sommerfeld constant. We have investigated the dynamics of detector signals due to X-ray events as shown in Fig. 2 for two different bias voltages.

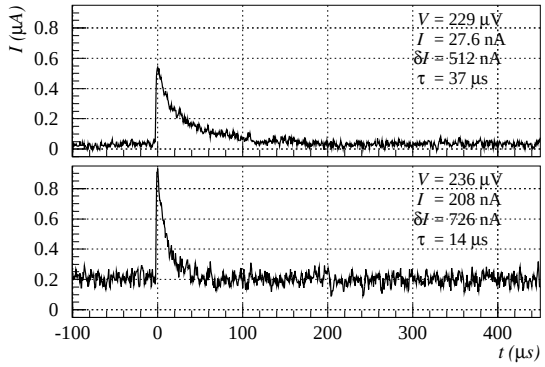

Fig. 2. Measured SINIS detector signals from X-ray events at two different operation points. Note the change in signal dynamics (decay time).

For this type of experiment we have typically chosen low $_n$ devices since the self-cooling power is predicted [3] to increase with increasing barrier transparency, i.e. P_{tun} / R_n^{-1}. However, the junctions with the thinnest oxide barriers revealed a partial suppression of the gap on the superconducting electrode side due to proximity of the ferromagnetic impurities (see IV in Fig. 3a). In order to keep the X-ray induced T and I variations small to maintain the simple model approach, a rather large (5 m thick) absorber volume was used. Detector signals were recorded over the bias voltage

range of sufficient sensitivity and fitted to the analytical model to extract the (essentially exponential) pulse decay time τ, which is plotted in Fig. 3c.

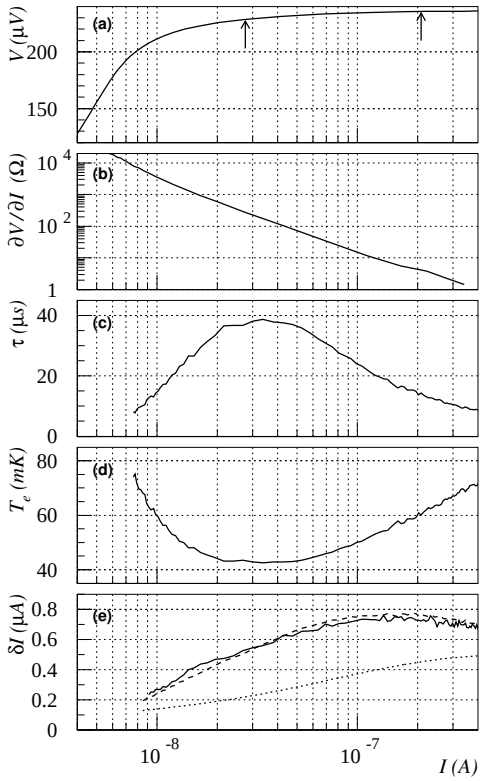

Fig. 3. (a) Measured IV characteristics of a low $_n$ SINIS device at 88 mK. The deviation from exponential behaviour at low currents (< 10 nA) is due to leakage onset. The arrows indicate the operation points for the signals shown in Fig. 2. The abscissa was converted to display current (instead of bias voltage) for improved visibility in the relevant range. (b) Corresponding differential resistance. (c) Decay time of measured detector signals upon deposition of 6 keV X-rays. (d) Deduced effective electron base temperature T_e of the absorber. (e) Measured current signal amplitude (solid line). The dashed line is a theoretical calculation assuming an effective T_e as shown in (d), whereas the dotted line assumes T_e = 88 mK.

Using Eqs. (1,2) and neglecting the effect of backheating we can calculate an effective T_e from and for given device parameters, as shown in Fig. 3d. Due to its T_e^5 dependence the value of T_e is not very sensitive to modest variations of model parameters. In Fig. 3e we plot the measured X-ray event signal amplitudes (solid line) together with theoretical calculations using an electron temperature as determined in Fig. 3d (dashed line) as well as for T_e = 88 mK (dotted line). Note the excellent agreement between experimental data and theory assuming a variable T_e, and the increase in sensitivity compared to a model without self-cooling. The effect of microrefrigeration compensates (in our case) at least for the power load from background radiation.

In spite of the remarkable consistency between measurements and our simple model, degradation due to backheating should in most cases be considered. Technically, the effect can be reduced by very thick electrodes or implementation of trapping layers [9]. Furthermore, we observed an indication of incomplete thermalization and partial phonon escape from the absorber. This was reflected by a relatively poor spectral energy resolution of our devices. Improvements are expected from deposition of the detector on a membrane [1] or fabrication of a fully suspended absorber bridge with small junction areas.

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